

P-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A) ^d	Q_g (Typ)
- 60	0.060 at $V_{GS} = - 10$ V	- 19	26
	0.077 at $V_{GS} = - 4.5$ V	- 16.8	

FEATURES

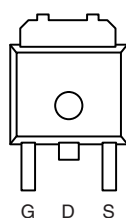
- TrenchFET[®] Power MOSFET
- 100 % UIS Tested


RoHS
COMPLIANT

APPLICATIONS

- High Side Switch for Full Bridge Converter
- DC/DC Converter for LCD Display

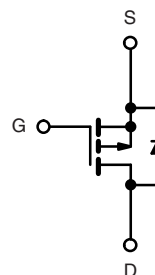
TO-252



Top View

Drain Connected to Tab

Ordering Information: SUD19P06-60-E3 (Lead (Pb)-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	- 60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C)	$T_C = 25$ °C	I_D	A
	$T_C = 125$ °C	- 18.3	
Pulsed Drain Current	I_{DM}	- 30	
Avalanche Current, Single Pulse	I_{AS}	- 22	
Repetitive Avalanche Energy, Single Pulse ^a	E_{AS}	24.2	mJ
Power Dissipation	$T_C = 25$ °C	P_D	W
	$T_A = 25$ °C	38.5 ^c 2.3 ^{b, c}	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^b	R_{thJA}	17	21	°C/W
		45	55	
Maximum Junction-to-Case	R_{thJC}	2.7	3.25	

Notes:

a. Duty cycle ≤ 1 %.

b. When mounted on 1" square PCB (FR-4 material).

c. See SOA curve for voltage derating.

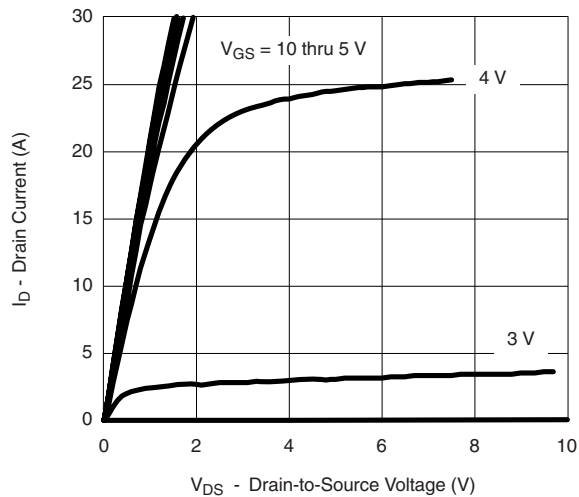
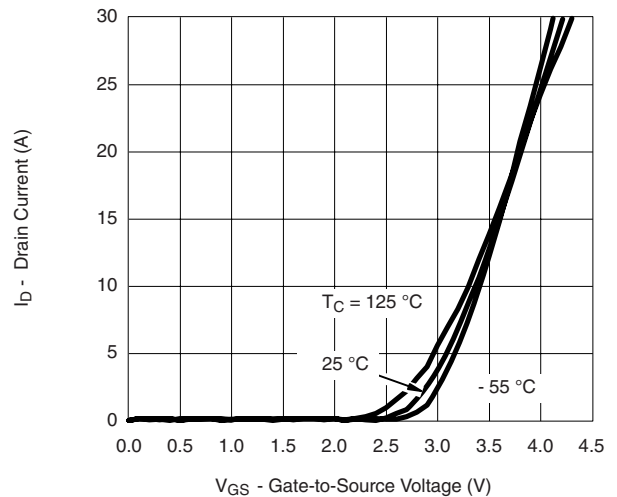
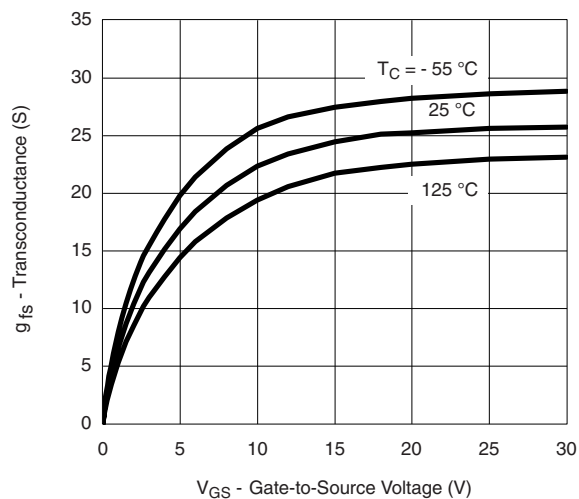
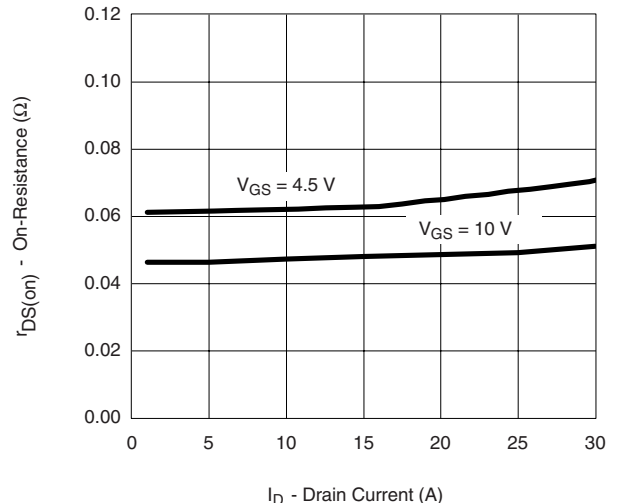
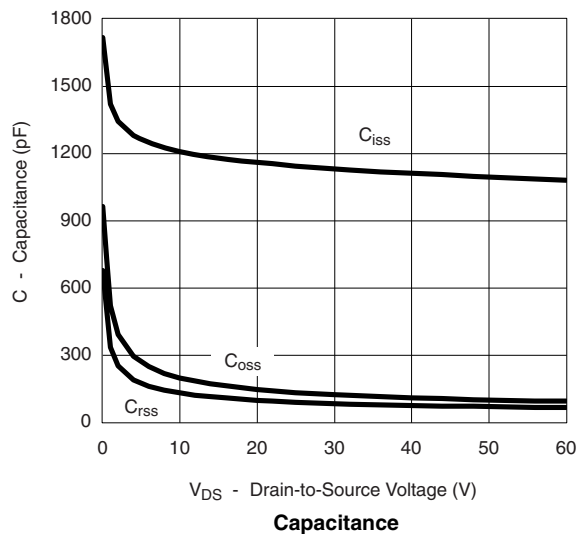
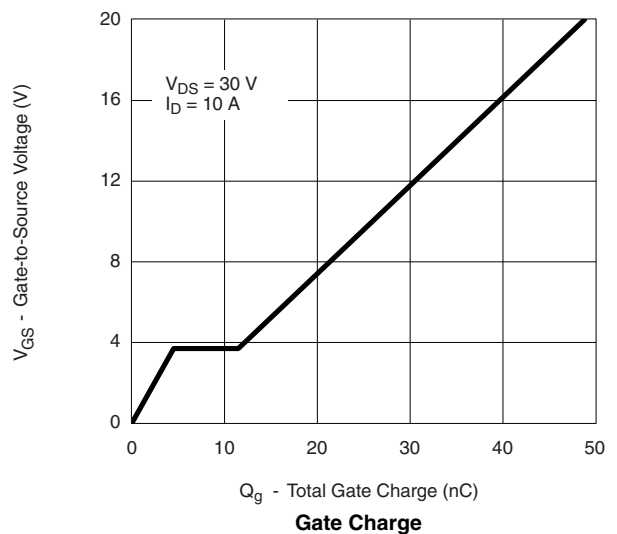
d. Based up on $T_C = 25$ °C.

SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 60			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 1		- 3	V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 60 V, V _{GS} = 0 V			- 1	μA
		V _{DS} = - 60 V, V _{GS} = 0 V, T _J = 125 °C			- 50	
		V _{DS} = - 60 V, V _{GS} = 0 V, T _J = 150 °C			- 125	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 10 V	- 30			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = - 10 V, I _D = - 10 A		0.048	0.060	Ω
		V _{GS} = - 10 V, I _D = - 10 A, T _J = 125 °C			0.102	
		V _{GS} = - 10 V, I _D = - 10 A, T _J = 150 °C			0.120	
		V _{GS} = - 4.5 V, I _D = - 5 A		0.061	0.077	
Forward Transconductance ^a	g _{fs}	V _{DS} = - 15 V, I _D = - 10 A		22		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = - 25 V, f = 1 MHz		1140	1710	pF
Output Capacitance	C _{oss}			130		
Reverse Transfer Capacitance	C _{rss}			90		
Total Gate Charge ^c	Q _g	V _{DS} = - 30 V, V _{GS} = - 10 V, I _D = - 10 A		26	40	nC
Gate-Source Charge ^c	Q _{gs}			4.5		
Gate-Drain Charge ^c	Q _{gd}			7.0		
Gate Resistance	R _g	f = 1 MHz		7.0		Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = - 30 V, R _L = 3 Ω I _D ≅ - 19 A, V _{GEN} = - 10 V, R _g = 2.5 Ω		8	15	ns
Rise Time ^c	t _r			9	15	
Turn-Off Delay Time ^c	t _{d(off)}			65	100	
Fall Time ^c	t _f			30	45	
Drain-Source Body Diode and Characteristics (T _C = 25 °C) ^b						
Continuous Current	I _S				- 30	A
Pulsed Current	I _{SM}				- 30	
Forward Voltage ^a	V _{SD}	I _F = - 19 A, V _{GS} = 0 V		- 1.0	- 1.5	V
Reverse Recovery Time	t _{rr}	I _F = - 19 A, di/dt = 100 A/μs		41	61	ns

Notes:

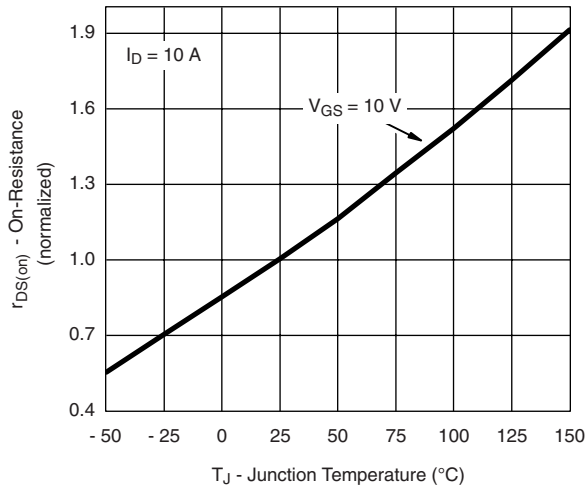
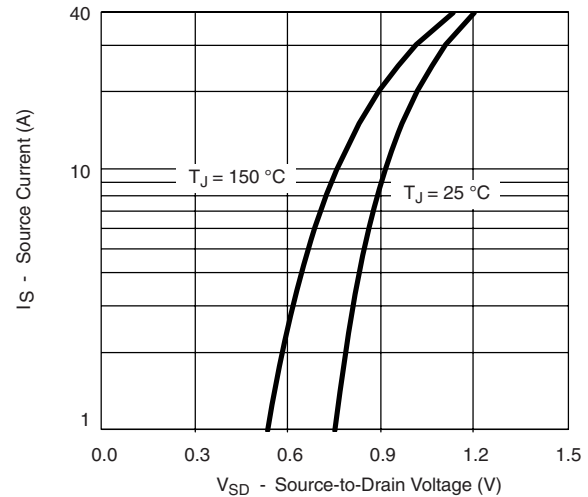
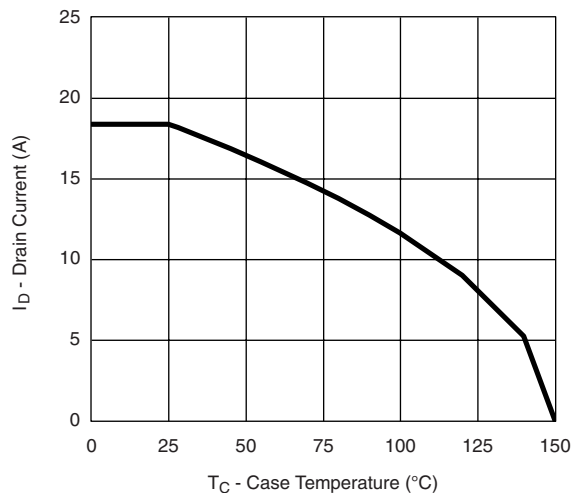
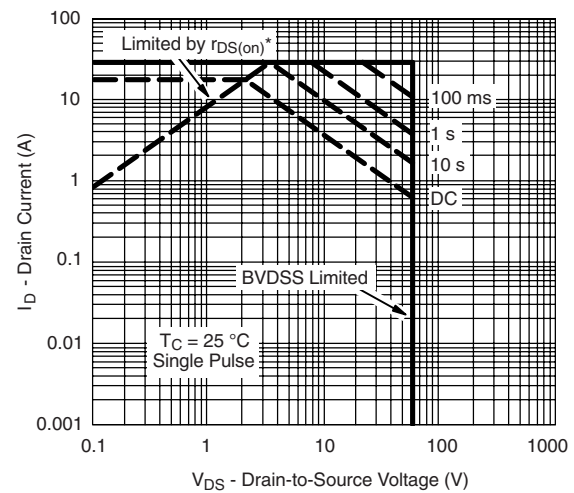
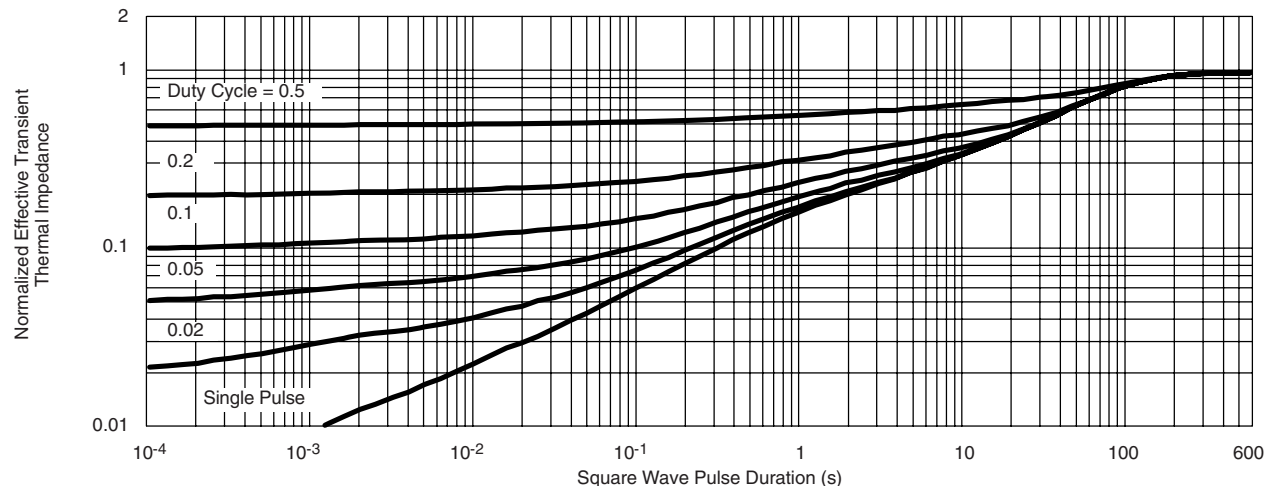
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

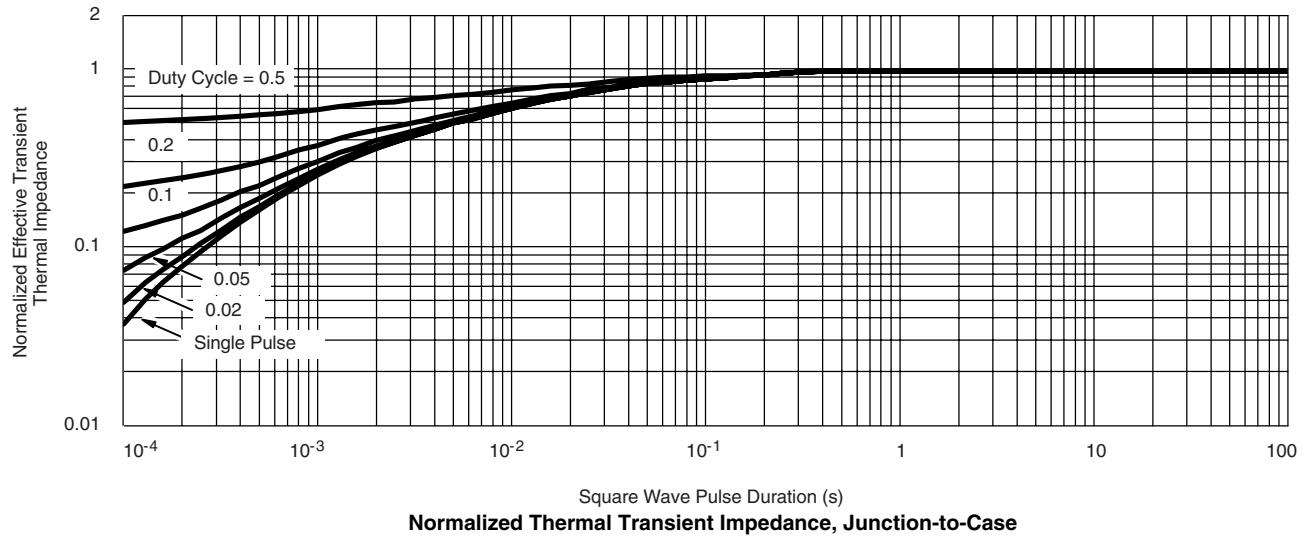
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted**Output Characteristics****Transfer Characteristics****Transconductance****On-Resistance vs. Drain Current****Capacitance****Gate Charge**

SUD19P06-60

Vishay Siliconix

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted**On-Resistance vs. Junction Temperature****Source-Drain Diode Forward Voltage****THERMAL RATINGS****Maximum Drain Current vs. Case Temperature*** $V_{GS} >$ minimum V_{GS} at which $r_{DS(on)}$ is specified**Safe Operating Area****Normalized Thermal Transient Impedance, Junction-to-Ambient**

THERMAL RATINGS


Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?69253>.



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